

Abstract

Nonvolatile semiconductor memory cell and associated fabrication method

The invention relates to a nonvolatile semiconductor memory cell and to an associated fabrication method, a source region (7), a drain region (8) and a channel region lying in between being formed in a substrate (1). In order to realize locally delimited memory locations (LB, RB), an electrically non-conductive charge storage layer (3) situated on a first insulation layer (2) is divided by an interruption (U), thereby preventing, in particular, a lateral charge transport between the memory locations (LB, RB) and significantly improving the charge retention properties.

Figure 2